

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

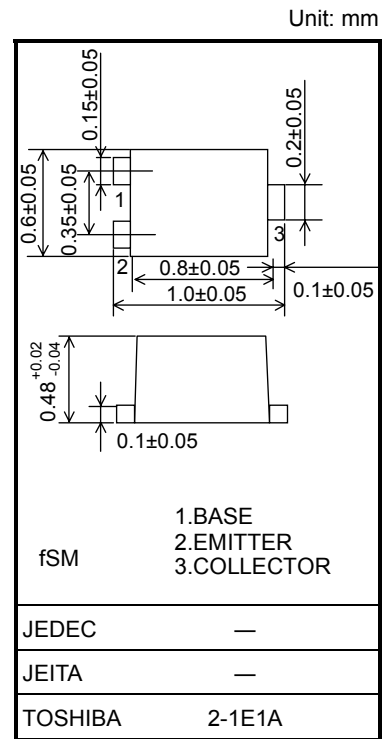
# 2SC6026

## General-Purpose Amplifier Applications

- High voltage and high current  
:  $V_{CE0} = 50\text{ V}$ ,  $I_C = 100\text{ mA}$  (max)
- Excellent  $h_{FE}$  linearity :  $h_{FE}(I_C = 0.1\text{ mA})/h_{FE}(I_C = 2\text{ mA}) = 0.95$  (typ.)
- High  $h_{FE}$  :  $h_{FE} = 120\sim 400$
- Complementary to 2SA2154
- Lead (Pb) free

## Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	60	V
Collector-emitter voltage	$V_{CEO}$	50	V
Emitter-base voltage	$V_{EBO}$	5	V
Collector current	$I_C$	100	mA
Base current	$I_B$	30	mA
Collector power dissipation	$P_C$	50	mW
Junction temperature	$T_j$	150	°C
Storage temperature range	$T_{stg}$	-55~150	°C



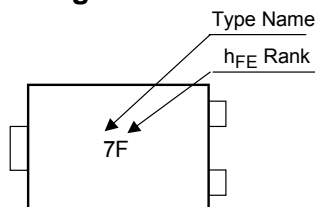
Weight: 0.0006 g (typ.)

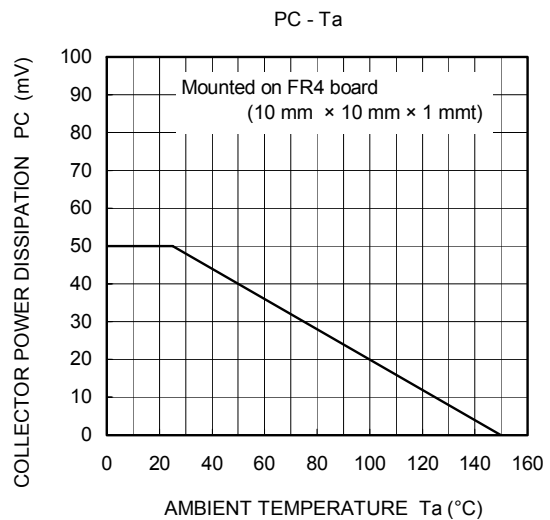
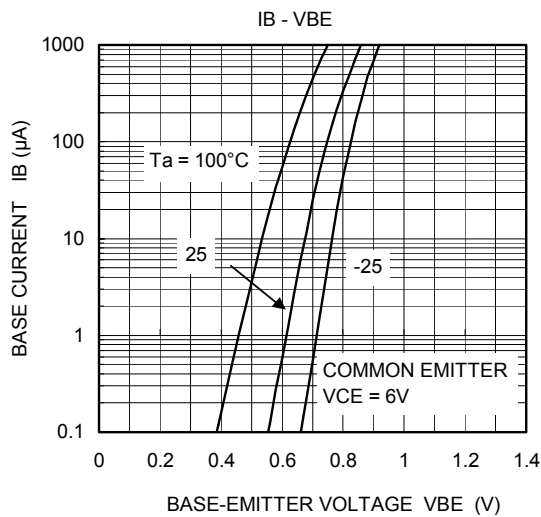
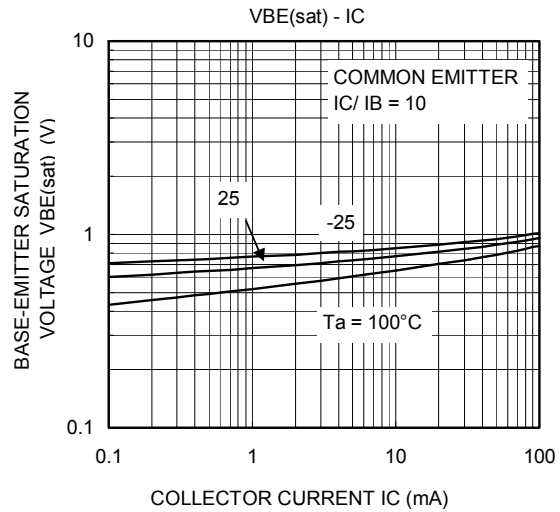
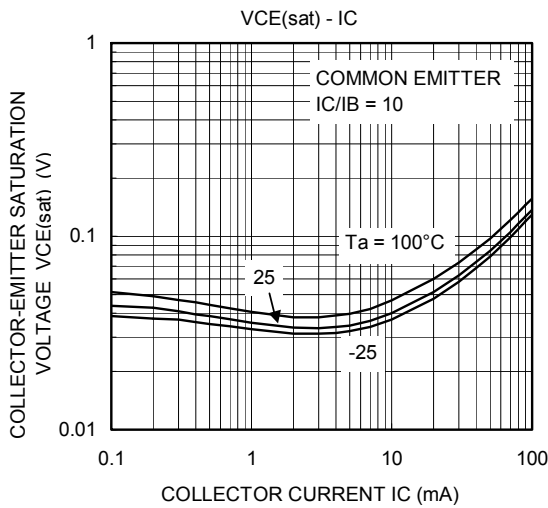
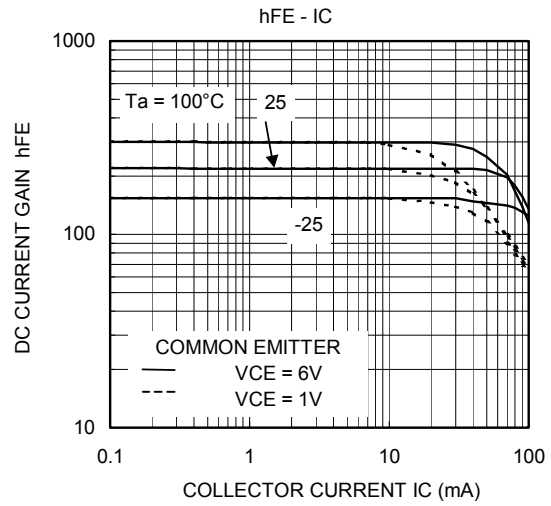
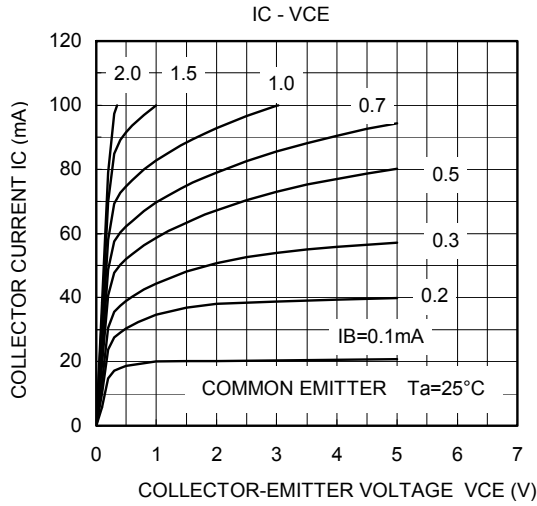
## Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = 60\text{ V}$ , $I_E = 0$	—	—	0.1	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = 5\text{ V}$ , $I_C = 0$	—	—	0.1	$\mu\text{A}$
DC current gain	$h_{FE}$ (Note)	$V_{CE} = 6\text{ V}$ , $I_C = 2\text{ mA}$	120	—	400	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100\text{ mA}$ , $I_B = 10\text{ mA}$	—	0.1	0.25	V
Transition frequency	$f_T$	$V_{CE} = 10\text{ V}$ , $I_C = 1\text{ mA}$	60	—	—	MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = 10\text{ V}$ , $I_E = 0$ , $f = 1\text{ MHz}$	—	0.95	—	pF

Note:  $h_{FE}$  classification Y (F): 120~240, GR (H): 200~400  
( ) marking symbol

## Marking





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